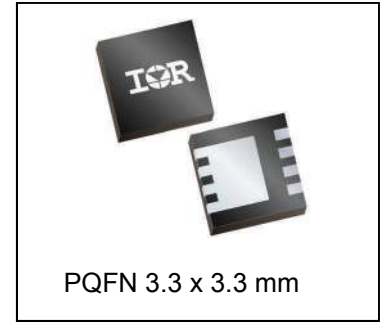
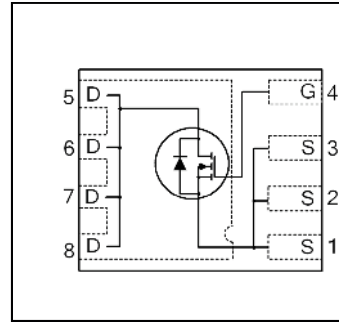


$V_{DSS}$	<b>30</b>	<b>V</b>
$R_{DS(on) \max}$ (@ $V_{GS} = 10V$ )	<b>4.3</b>	<b>mΩ</b>
$Qg$ (typical)	<b>13</b>	<b>nC</b>
$Rg$ (typical)	<b>1.1</b>	<b>Ω</b>
$I_D$ (@ $T_C$ (Bottom) = 25°C)	<b>40</b> Ⓞ	<b>A</b>



**Applications**

- Synchronous MOSFET for Buck Converters

**Features**

Low $R_{DS(on)}$ (< 4.3mΩ)
Schottky intrinsic diode with low forward voltage
Low Thermal Resistance to PCB (<3.4°C/W)
100% $Rg$ tested
Low Profile (< 1.0 mm)
Industry-Standard Pinout
Compatible with Existing Surface Mount Techniques
RoHS Compliant Containing no Lead, no Bromide and no Halogen
MSL1, Industrial Qualification

results in  
 ⇒

**Benefits**

Lower Conduction Losses
Low Switching Losses
Increased Power Density
Increased Reliability
Increased Power Density
Multi-Vendor Compatibility
Easier Manufacturing
Environmentally Friendlier
Increased Reliability

Orderable part number	Package Type	Standard Pack		Note
		Form	Quantity	
IRFHM830DTRPbF	PQFN 3.3mm x 3.3mm	Tape and Reel	4000	
IRFHM830DTR2PbF	PQFN 3.3mm x 3.3mm	Tape and Reel	400	EOL notice # 259

**Absolute Maximum Ratings**

	Parameter	Max.	Units
$V_{DS}$	Drain-to-Source Voltage	30	V
$V_{GS}$	Gate-to-Source Voltage	± 20	
$I_D$ @ $T_A = 25^\circ C$	Continuous Drain Current, $V_{GS}$ @ 10V	20	A
$I_D$ @ $T_A = 70^\circ C$	Continuous Drain Current, $V_{GS}$ @ 10V	16	
$I_D$ @ $T_C(Bottom) = 25^\circ C$	Continuous Drain Current, $V_{GS}$ @ 10V	40Ⓞ	
$I_D$ @ $T_C(Bottom) = 100^\circ C$	Continuous Drain Current, $V_{GS}$ @ 10V	40Ⓞ	
$I_{DM}$	Pulsed Drain Current ①	160	
$P_D$ @ $T_A = 25^\circ C$	Power Dissipation ⑤	2.7	W
$P_D$ @ $T_C(Bottom) = 25^\circ C$	Power Dissipation ⑤	37	
	Linear Derating Factor ⑤	0.022	W/°C
$T_J$ $T_{STG}$	Operating Junction and Storage Temperature Range	-55 to + 150	°C

Notes ① through ⑥ are on page 9

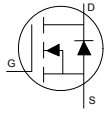
**Static @ T<sub>J</sub> = 25°C (unless otherwise specified)**

	Parameter	Min.	Typ.	Max.	Units	Conditions
BV <sub>DSS</sub>	Drain-to-Source Breakdown Voltage	30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 1mA
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	Breakdown Voltage Temp. Coefficient	—	0.02	—	V/°C	Reference to 25°C, I <sub>D</sub> = 4mA
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance	—	3.4	4.3	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 20A ③
		—	5.7	7.1		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 20A ③
V <sub>GS(th)</sub>	Gate Threshold Voltage	1.35	1.8	2.35	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 50μA
ΔV <sub>GS(th)</sub>	Gate Threshold Voltage Coefficient	—	-6.0	—	mV/°C	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 1mA
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	500	μA	V <sub>DS</sub> = 24V, V <sub>GS</sub> = 0V
		—	—	5.0	mA	V <sub>DS</sub> = 24V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 125°C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	—	—	100	nA	V <sub>GS</sub> = 20V
	Gate-to-Source Reverse Leakage	—	—	-100		V <sub>GS</sub> = -20V
g <sub>fs</sub>	Forward Transconductance	69	—	—	S	V <sub>DS</sub> = 15V, I <sub>D</sub> = 20A
Q <sub>g</sub>	Total Gate Charge	—	27	—	nC	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 15V, I <sub>D</sub> = 20A  V <sub>DS</sub> = 15V V <sub>GS</sub> = 4.5V I <sub>D</sub> = 20A See Fig.17 & 18
Q <sub>g</sub>	Total Gate Charge	—	13	20		
Q <sub>gs1</sub>	Pre-V <sub>th</sub> Gate-to-Source Charge	—	2.9	—		
Q <sub>gs2</sub>	Post-V <sub>th</sub> Gate-to-Source Charge	—	1.8	—		
Q <sub>gd</sub>	Gate-to-Drain Charge	—	4.5	—		
Q <sub>godr</sub>	Gate Charge Overdrive	—	3.8	—		
Q <sub>sw</sub>	Switch Charge (Q <sub>gs2</sub> + Q <sub>gd</sub> )	—	6.3	—	nC	V <sub>DS</sub> = 16V, V <sub>GS</sub> = 0V
R <sub>G</sub>	Gate Resistance	—	1.1	—	Ω	
t <sub>d(on)</sub>	Turn-On Delay Time	—	9.8	—	ns	V <sub>DD</sub> = 15V, V <sub>GS</sub> = 4.5V I <sub>D</sub> = 20A R <sub>G</sub> = 1.8Ω See Fig.15
t <sub>r</sub>	Rise Time	—	20	—		
t <sub>d(off)</sub>	Turn-Off Delay Time	—	9.1	—		
t <sub>f</sub>	Fall Time	—	6.7	—		
C <sub>iss</sub>	Input Capacitance	—	1797	—	pF	V <sub>GS</sub> = 0V V <sub>DS</sub> = 25V f = 1.0MHz
C <sub>oss</sub>	Output Capacitance	—	363	—		
C <sub>rss</sub>	Reverse Transfer Capacitance	—	148	—		

**Avalanche Characteristics**

	Parameter	Typ.	Max.	Units
E <sub>AS</sub> (Thermally limited)	Single Pulse Avalanche Energy ②	—	82	mJ
I <sub>AR</sub>	Avalanche Current ①	—	20	A

**Diode Characteristics**

	Parameter	Min.	Typ.	Max.	Units	Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	40⑥	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I <sub>SM</sub>	Pulsed Source Current (Body Diode) ①	—	—	160		
V <sub>SD</sub>	Diode Forward Voltage	—	—	0.85	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = 20A, V <sub>GS</sub> = 0V ③
t <sub>rr</sub>	Reverse Recovery Time	—	16	24	ns	T <sub>J</sub> = 25°C, I <sub>F</sub> = 20A, V <sub>DD</sub> = 15V
Q <sub>rr</sub>	Reverse Recovery Charge	—	17	26	nC	di/dt = 300A/μs ③

**Thermal Resistance**

	Parameter	Typ.	Max.	Units
R <sub>θJC</sub> (Bottom)	Junction-to-Case ④	—	3.4	°C/W
R <sub>θJC</sub> (Top)	Junction-to-Case ④	—	37	
R <sub>θJA</sub>	Junction-to-Ambient ⑤	—	46	
R <sub>θJA</sub> (<10s)	Junction-to-Ambient ⑤	—	31	

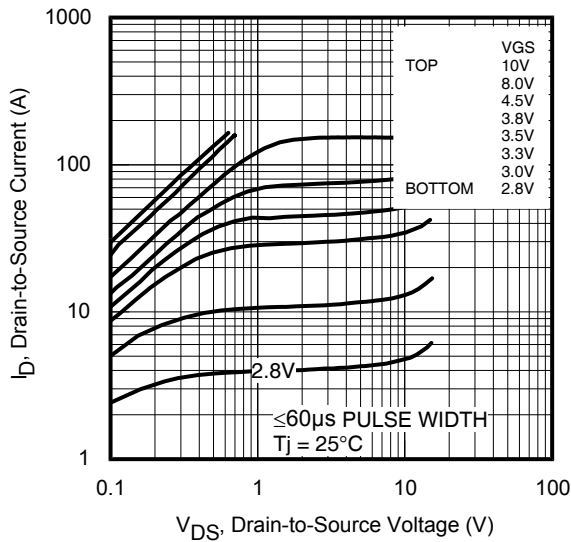


Fig 1. Typical Output Characteristics

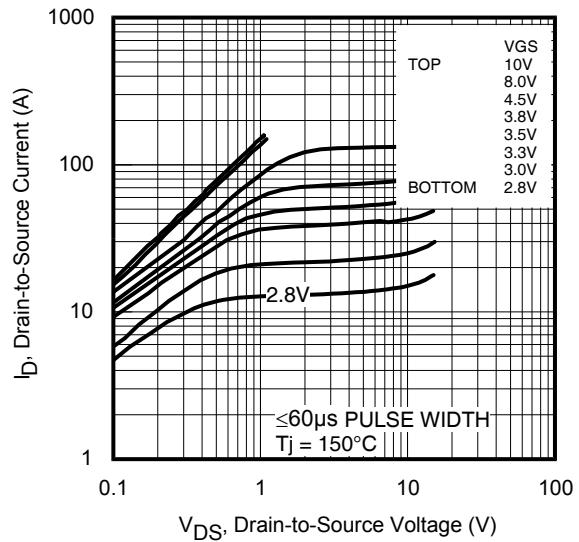


Fig 2. Typical Output Characteristics

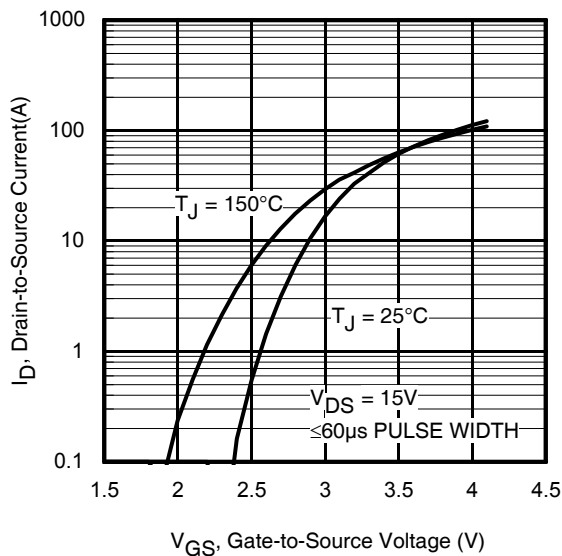


Fig 3. Typical Transfer Characteristics

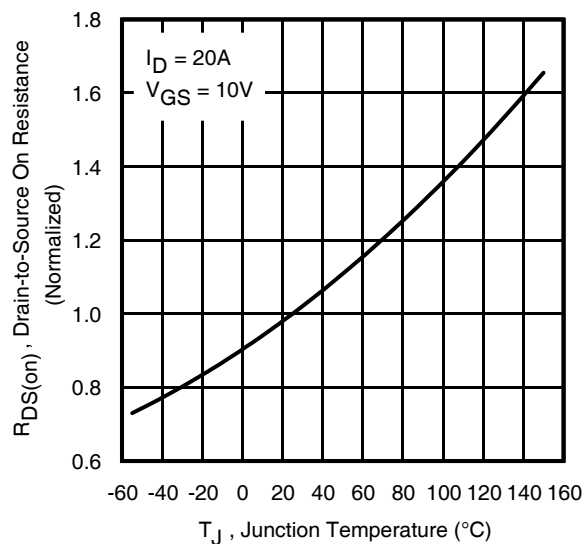


Fig 4. Normalized On-Resistance vs. Temperature

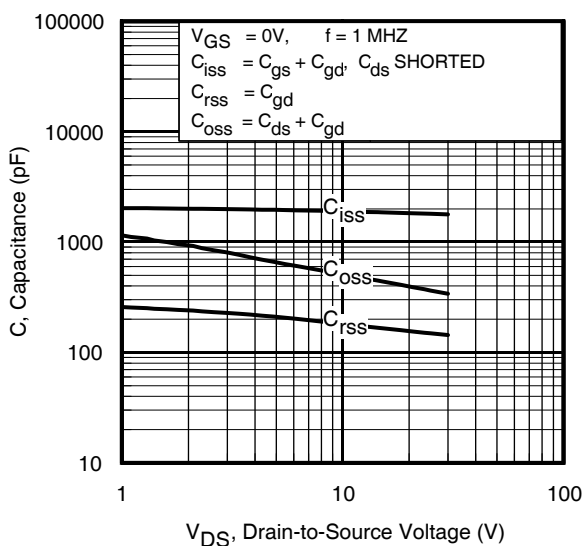


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

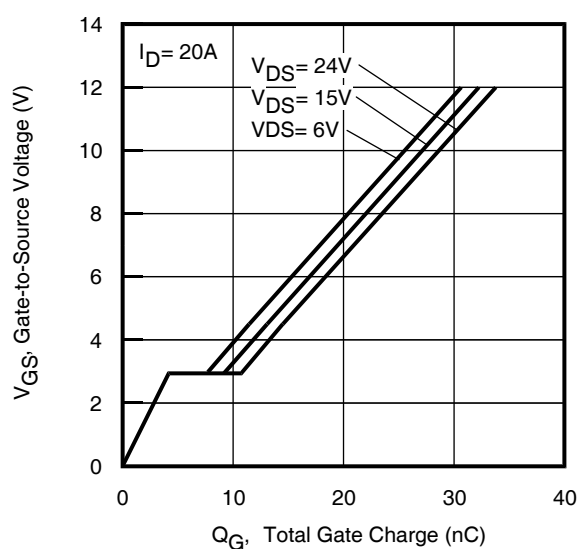


Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage

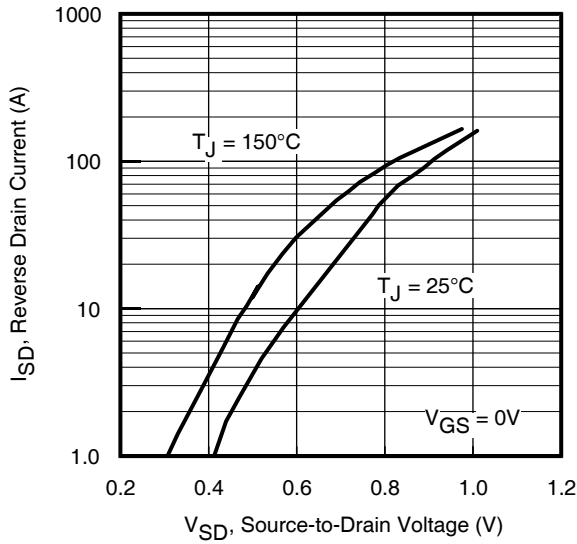


Fig 7. Typical Source-Drain Diode Forward Voltage

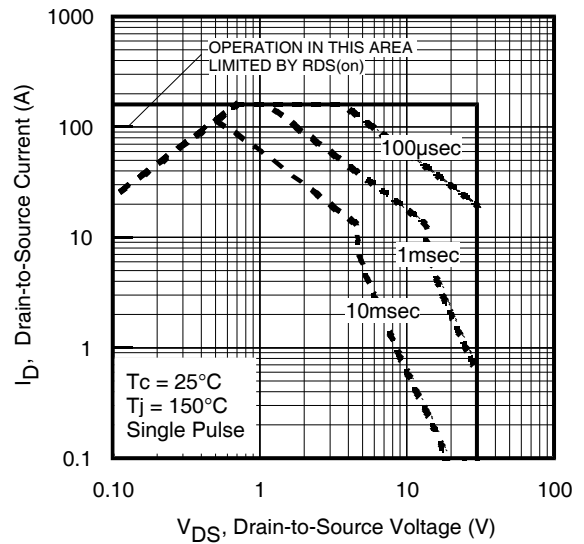


Fig 8. Maximum Safe Operating Area

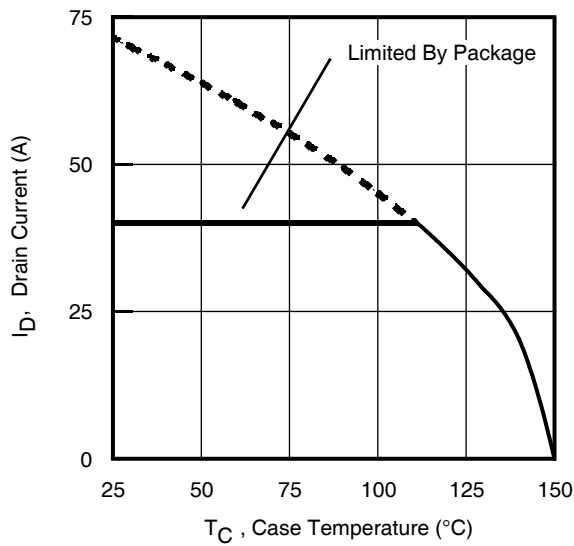


Fig 9. Maximum Drain Current vs. Case Temperature

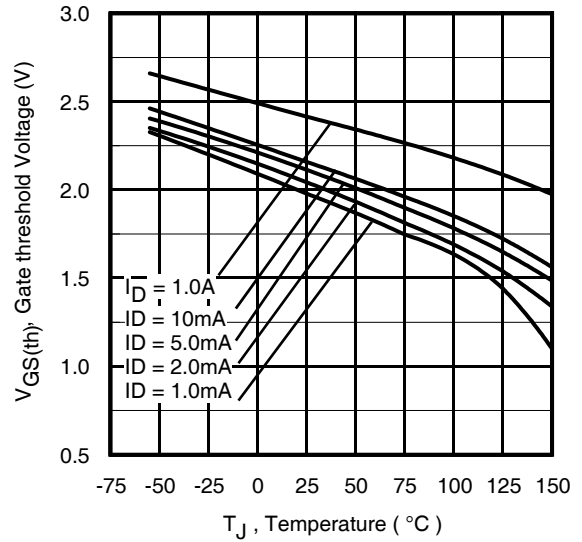


Fig 10. Threshold Voltage Vs. Temperature

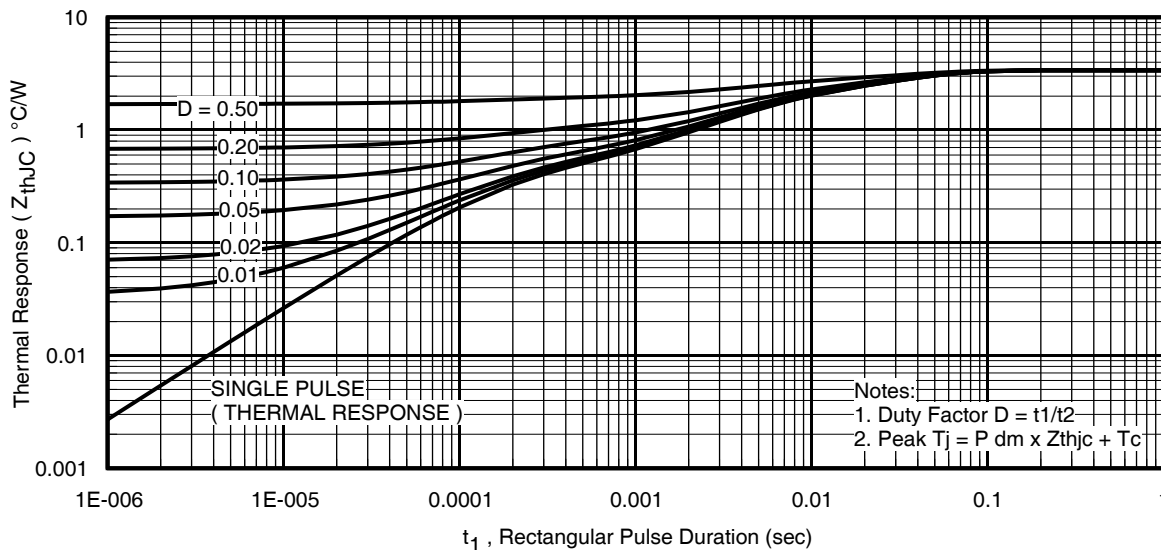
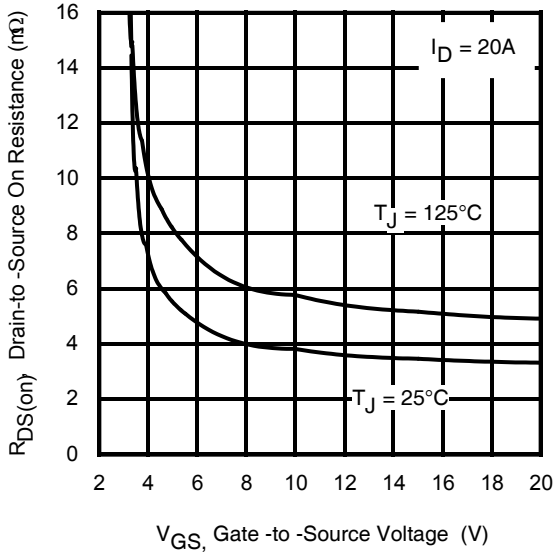
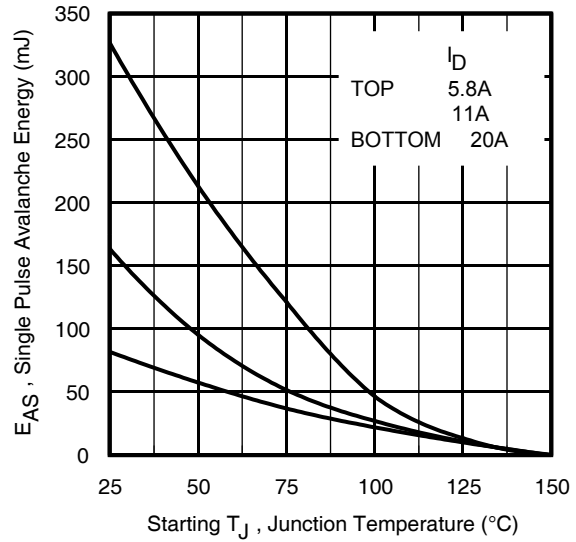


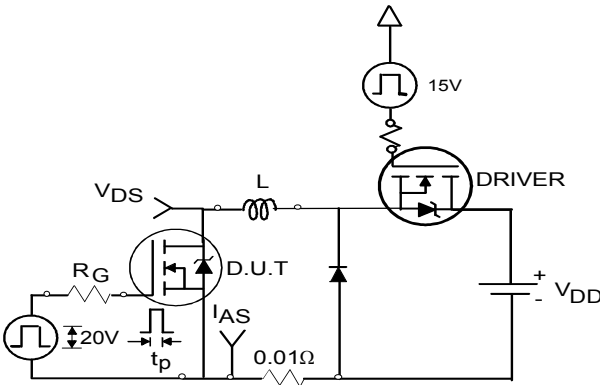
Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case



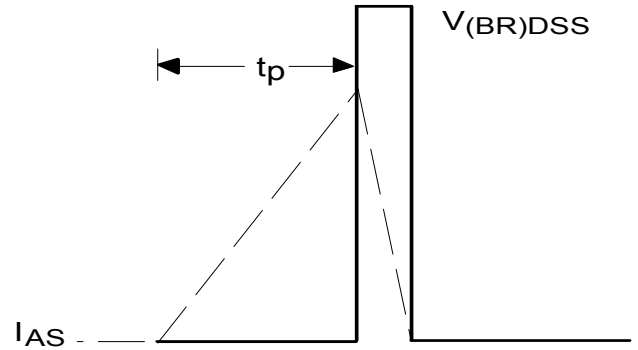
**Fig 12.** On-Resistance vs. Gate Voltage



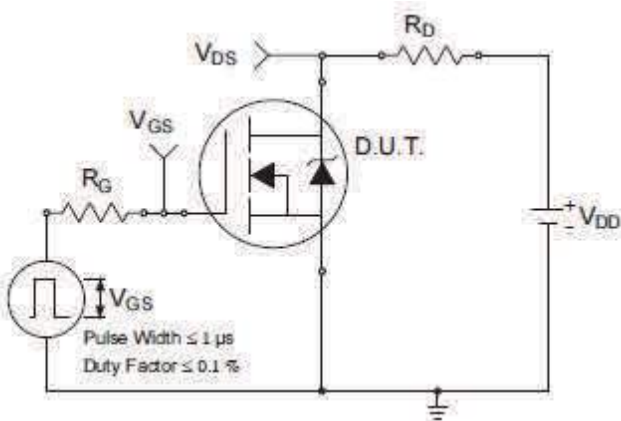
**Fig 13.** Maximum Avalanche Energy vs. Drain Current



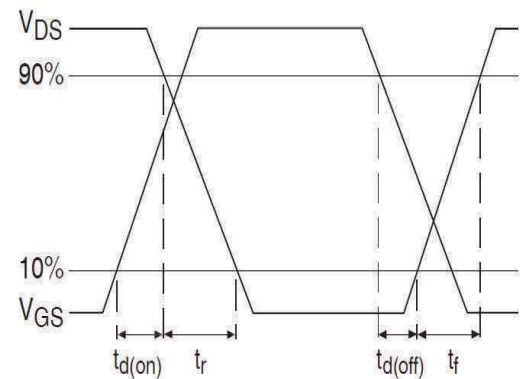
**Fig 14a.** Unclamped Inductive Test Circuit



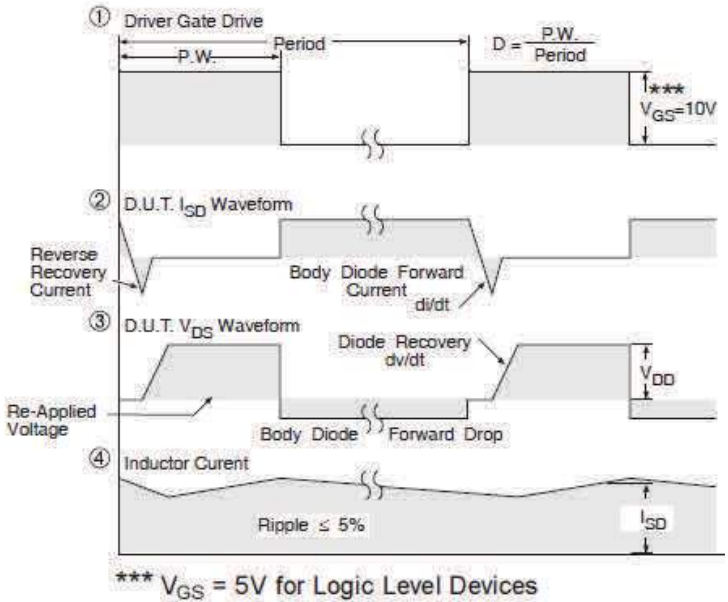
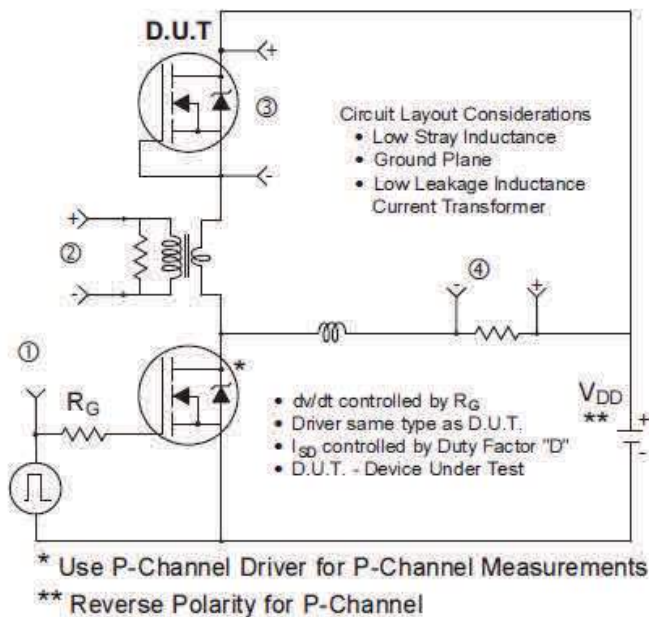
**Fig 14b.** Unclamped Inductive Waveforms



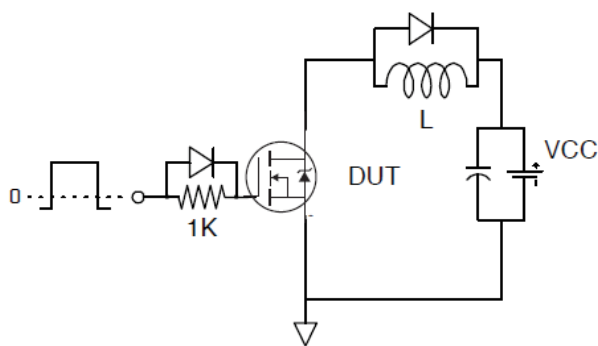
**Fig 15a.** Switching Time Test Circuit



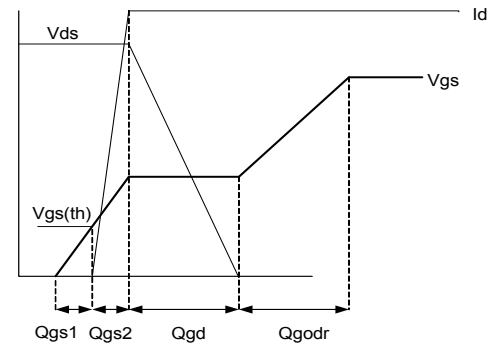
**Fig 15b.** Switching Time Waveforms



**Fig 16.** Peak Diode Recovery  $dv/dt$  Test Circuit for N-Channel HEXFET<sup>®</sup> Power MOSFETs

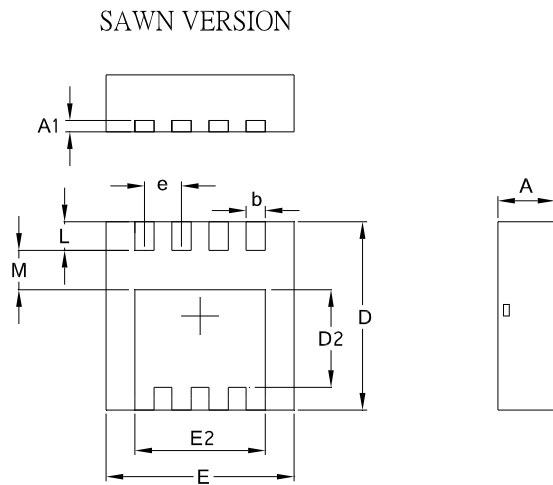


**Fig 17.** Gate Charge Test Circuit



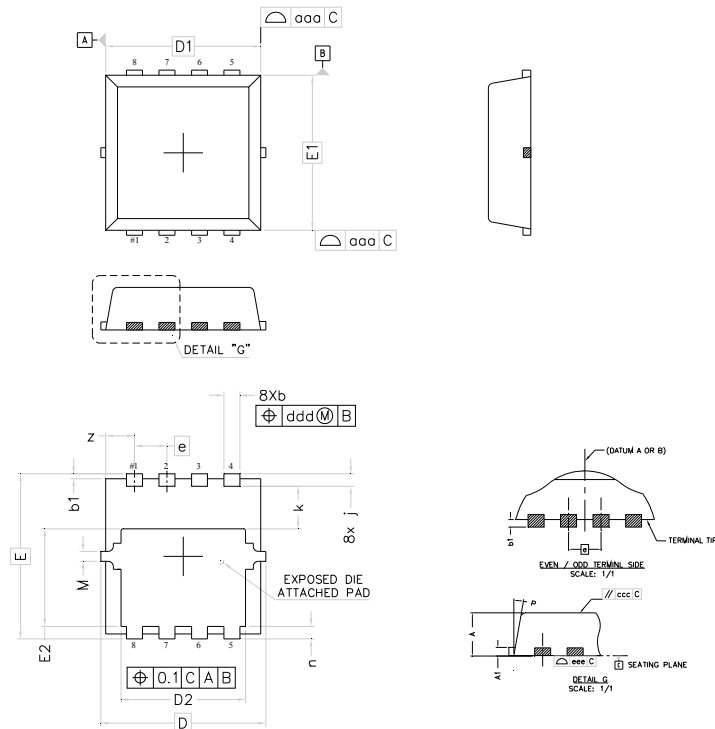
**Fig 18.** Gate Charge Waveform

## PQFN 3.3 x 3.3 Outline "B" Package Details



SYMBOL	COMMON			
	MM		INCH	
	MIN.	MAX.	MIN.	MAX.
A	0.70	1.05	0.0276	0.0413
A1	0.12	0.39	0.0047	0.0154
b	0.25	0.39	0.0098	0.0154
D	3.20	3.45	0.1260	0.1358
D1	3.00	3.20	0.1181	0.1417
D2	1.69	2.20	0.0665	0.0866
E	3.20	3.40	0.1260	0.1339
E1	3.00	3.20	0.1181	0.1417
E2	2.15	2.59	0.0846	0.1020
e	0.65 BSC		0.0256 BSC	
L	0.15	0.55	0.0059	0.0217
M	0.59	—	0.0232	—
O	9Deg	12Deg	9Deg	12Deg

## PQFN 3.3 x 3.3 Outline "G" Package Details



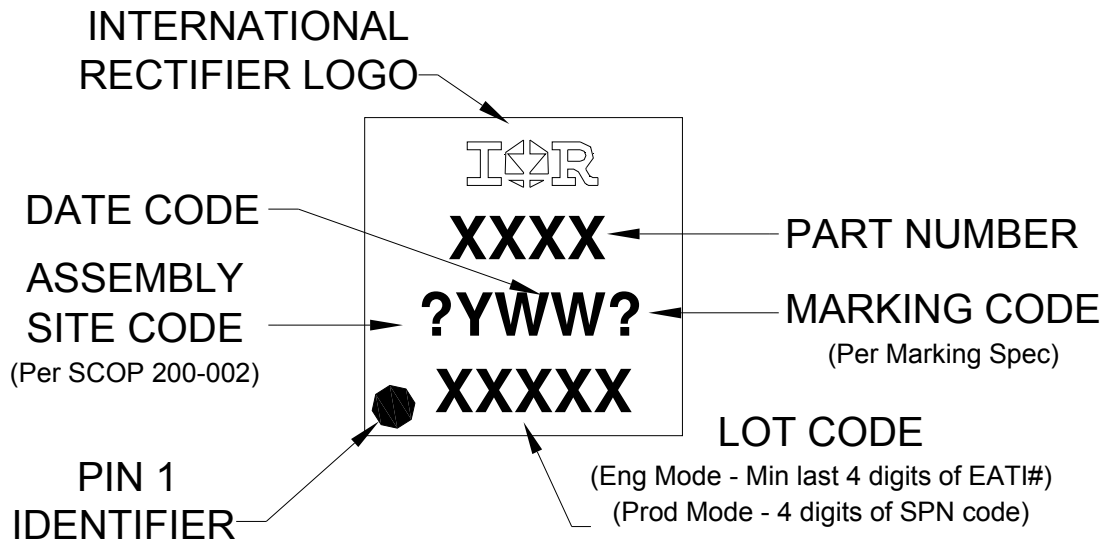
DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.80	0.90	.0315	.0354
A1	0.12	0.22	.0047	.0086
b	0.22	0.42	.0087	.0165
b1	0.05	0.15	.0020	.0059
D	3.30 BSC		.1299 BSC	
D1	3.10 BSC		.1220 BSC	
D2	2.29	2.69	.0902	.1059
E	3.30 BSC		.1299 BSC	
E1	3.10 BSC		.1220 BSC	
E2	1.85	2.05	.0728	.0807
e	0.65 BSC		.0255 BSC	
j	0.15	0.35	.0059	.0137
k	0.75	0.95	.0295	.0374
n	0.15	0.35	.0059	.0137
M	NOM.	0.20	NOM.	.0078
P	9°	11°	9°	11°

For more information on board mounting, including footprint and stencil recommendation, please refer to application note AN-1136: <http://www.irf.com/technical-info/appnotes/an-1136.pdf>

For more information on package inspection techniques, please refer to application note AN-1154:

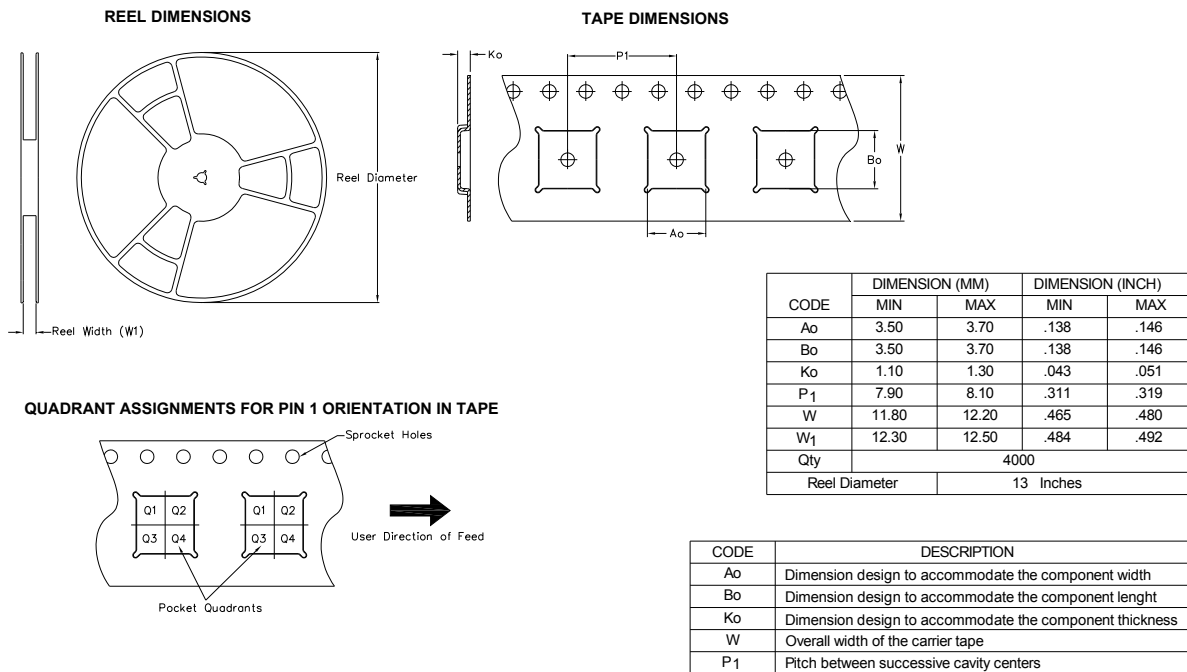
<http://www.irf.com/technical-info/appnotes/an-1154.pdf>

## PQFN 3.3 x 3.3 Part Marking



Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

## PQFN 3.3 x 3.3 Tape and Reel



Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>



**Qualification Information†**

<b>Qualification Level</b>	Industrial (per JEDEC JESD47F <sup>††</sup> guidelines)	
<b>Moisture Sensitivity Level</b>	PQFN 3.3mm x 3.3mm	MSL1 (per JEDEC J-STD-020D <sup>††</sup> )
<b>RoHS Compliant</b>	Yes	

† Qualification standards can be found at International Rectifier's web site: <http://www.irf.com/product-info/reliability>

†† Applicable version of JEDEC standard at the time of product release.

**Notes:**

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting  $T_J = 25^{\circ}\text{C}$ ,  $L = 0.409\text{mH}$ ,  $R_G = 50\Omega$ ,  $I_{AS} = 12\text{A}$ .
- ③ Pulse width  $\leq 400\mu\text{s}$ ; duty cycle  $\leq 2\%$ .
- ④  $R_{\theta}$  is measured at  $T_J$  of approximately  $90^{\circ}\text{C}$ .
- ⑤ When mounted on 1 inch square PCB (FR-4). Please refer to AN-994 for more details:  
<http://www.irf.com/technical-info/appnotes/an-994.pdf>
- ⑥ Calculated continuous current based on maximum allowable junction temperature. Package is limited to 40A by production test capability.

<b>Revision History</b>	
<b>Date</b>	<b>Comments</b>
12/16/2013	<ul style="list-style-type: none"> <li>• Updated ordering information to reflect the End-Of-life (EOL) of the mini-reel option (EOL notice #259)</li> <li>• Updated data sheet with new IR corporate template</li> </ul>
6/6/2014	<ul style="list-style-type: none"> <li>• Updated schematic on page 1</li> <li>• Updated part marking on page 7.</li> <li>• Updated Tape and Reel on page 8.</li> </ul>
9/25/2015	<ul style="list-style-type: none"> <li>• Updated package outline to reflect the PCN # (67-PCN90-Public-R2) for "option B" and added package outline for "option G" on page 7</li> <li>• Updated "IFX" logo on all pages.</li> </ul>